

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

- 1-24. (Cancelled)
25. (Previously Presented) A method of manufacturing an integrated circuit comprising:
- forming trenches in a substrate comprising a germanium-containing layer;
  - providing a strained semiconductor material above the germanium-containing layer and on sidewalls of the trenches; and
  - providing insulative material in the trenches to form trench isolation regions.
26. (Currently Amended) The method of claim 25, wherein the strained semiconductor material is formed on the sidewalls of the trenches.
27. (Previously Presented) The method of claim 25, further comprising siliciding the strained semiconductor material.
28. (Previously Presented) The method of claim 25, wherein the germanium-containing layer comprises a silicon-germanium material.
29. (Previously Presented) The method of claim 25, wherein the strained semiconductor material comprises strained silicon.
30. (Previously Presented) The method of claim 25, wherein the insulative material comprises silicon dioxide.
31. (Previously Presented) The method of claim 25, further providing a first layer above a buried oxide layer.

32. (Previously Presented) The method of claim 31, wherein the trenches extend through the germanium-containing layer to the buried oxide layer.
33. (Previously Presented) A method of producing an integrated circuit comprising:  
forming a trench having sidewalls in a substrate comprising a silicon-germanium layer;  
forming a strained silicon material above the silicon-germanium layer and on the sidewalls of the trench; and  
filling the trench with an insulative material to form a trench isolation region.
34. (Previously Presented) The method of claim 33, wherein the strained silicon material is formed on sidewalls of the trench.
35. (Previously Presented) The method of claim 33, further comprising siliciding the strained silicon material.
36. (Previously Presented) The method of claim 33, wherein the trench extends through the silicon-germanium layer to an underlying buried oxide layer.